

In the Claims

Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 CFR § 1.121(c)(1)(i). Cancel all previous versions of any pending claim.

A marked-up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 CFR § 1.121(c)(1)(ii). Any claim not accompanied by a marked-up version has not been changed relative to the immediate prior version, except that marked-up versions are not being supplied for any added claim or canceled claim.

CLAIMS

✓
Please cancel claims 49-54.

✓
Please add the following new claims:

sub
C3
69. (New) A semiconductor construction comprising:
a semiconductor substrate having a trench extending partially therein and
upper surfaces adjacent the trench;

an oxide layer formed over the upper surfaces of the semiconductor
substrate and having an uppermost surface; and

B²
an insulative material filling the trench and having a portion outward of the
trench and semiconductor substrate, the portion comprising an outermost upper
surface elevationally above the uppermost surface of the oxide layer and
sidewalls connecting the outermost upper surface with the oxide layer, the
connection between the sidewalls and the outermost upper surface comprising
curved corners, and the connection between the sidewalls and the oxide layer
comprising curved corners extending from elevationally above the oxide layer
downward to the uppermost surface of the oxide layer.

70. (New) The semiconductor construction of claim 69 wherein the
insulative material comprises oxide.

71. (New) The semiconductor construction of claim 69 wherein the
insulative material comprises a first insulative material partially filling the trench
and a second insulative material formed over the first insulative material.

B²
(Contd)
Considered
C³

72. (New) The semiconductor construction of claim 69 further comprising a polysilicon layer formed against the uppermost surface of the oxide layer and the portion of the insulative material.